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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. <b>40337</b>	SERIAL NO. <b>TBD</b>
<b>INFORMATION DISCLOSURE CITATION BY APPLICANT</b> <i>(USE SEVERAL SHEETS IF NECESSARY)</i>		APPLICANT: <b>Yasuyuki Naito et al.</b>	
		FILING DATE: <b>Herewith</b>	GROUP ART UNIT: <b>TBD</b>

## U.S. PATENT DOCUMENTS

Examiner Initial		Document No.	Date	Name	Class	Subclass	Filing Date If Appropriate
	A						
	B						
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## FOREIGN PATENT DOCUMENTS

		Document No.	Date	Country	Class	Subclass	Translation
No Copies	L	<del>1-114111</del>	<del>05/1989</del>	<del>JAPAN</del>			<del>Cited on ISR</del>
	M	<del>2-52514</del>	<del>02/1990</del>	<del>JAPAN</del>			<del>Cited on ISR</del>
	N	<del>2003-289449</del>	<del>10/2003</del>	<del>JAPAN</del>			<del>Cited on ISR</del>
	P						
	Q						

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

/BS/	R	Schloemann et al., "Epitaxial Fe films on GaAs for hybrid semiconductor-magnetic memories", 04/1988, pages 3140-3142 ( <del>Cited in Specification English Text</del> ) <b>Journal of Applied Physics</b>
	S	<b>Vol. 63, No. 8</b>
	T	

Examiner: /Barbara Summons/

Date Considered 04/16/2008

\*Examiner: Initial if reference considered, regardless of whether citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.